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PATENT
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re Application of:

Tadatomo et al.

Application No. 09/787,502

Art Unit: 2815

TECH CENTER 2800

Examiner: E. Ortiz

Filed: March 16, 2001

For: SEMICONDUCTOR LIGHT
RECEIVING ELEMENT

AMENDMENTS TO CLAIMS MADE IN RESPONSE
TO OFFICE ACTION DATED DECEMBER 3, 2001

*(Deletions to the claims are indicated by cross-out text,
while additions are indicated by underlined text)*

1. (Canceled)

2. (Amended) ~~The light receiving element of claim 1,~~ A semiconductor light receiving element comprising a light receiving layer comprising a GaN group semiconductor and an electrode formed on one surface of the light receiving layer as a light receiving surface in such a manner that the light can enter the light receiving layer, wherein the light receiving element is a Schottky barrier type light receiving element, said light receiving layer is a first conductivity type layer, said electrode formed on said light receiving surface comprises at least a Schottky electrode, and a total of boundary lines between areas of the light receiving surface covered with the Schottky electrode and exposed areas is longer than the length of the outer periphery of the light receiving surface.

8. (Amended) ~~The light receiving element of claim 1,~~ A semiconductor light receiving element comprising a light receiving layer comprising a GaN group semiconductor and an electrode formed on one surface of the light receiving layer as a light receiving surface in such a manner that the light can enter the light receiving layer, wherein the light receiving element is a photoconductive type light receiving element, the light receiving layer is a first conductivity type i layer, and the electrode formed on the light receiving surface is an ohmic electrode of one polarity, which element comprising an ohmic electrode of the other polarity formed on the other surface of the light receiving layer directly or via a first conductivity type and low resistance GaN group semiconductor layer.